TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

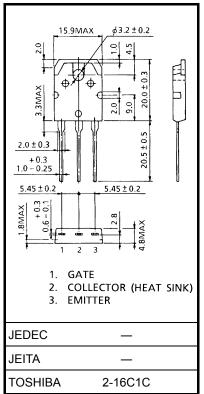
GT15Q102

High Power Switching Applications

- Third-generation IGBT
- Enhancement mode type
- High speed: $t_f = 0.32 \ \mu s \ (max)$
- Low saturation voltage: VCE (sat) = 2.7 V (max)

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	1200	V	
Gate-emitter voltage		V _{GES}	±20	V	
Collector current	DC	IC	15	А	
	1 ms	I _{CP}	30		
Collector power dissipation		Pc	170	W	
(Tc = 25°C)		ГC	170		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



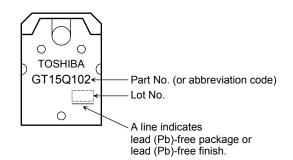
Weight: 4.6 g

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the

reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Marking

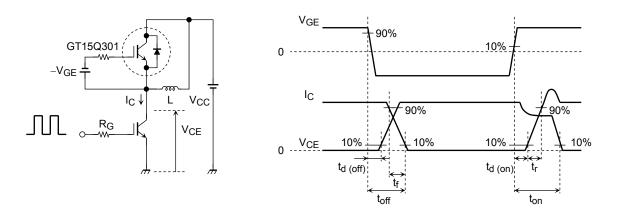


Unit: mm

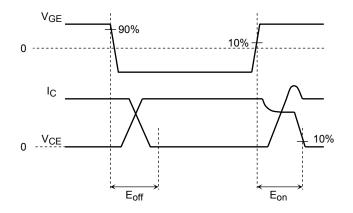
Electrical Characteristics (Ta = 25°C)

Chara	cteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage curre	ent	I _{GES}	$V_{GE} = \pm 20$ V, $V_{CE} = 0$	_	_	±500	nA
Collector cut-off cu	irrent	ICES	$V_{CE} = 1200 V, V_{GE} = 0$			1.0	mA
Gate-emitter cut-of	ff voltage	V _{GE (OFF)}	$I_{C} = 1.5 \text{ mA}, V_{CE} = 5 \text{ V}$	4.0		7.0	V
Collector-emitter s	aturation voltage	V _{CE (sat)}	I _C = 15 A, V _{GE} = 15 V	_	2.1	2.7	V
Input capacitance		Cies	$V_{CE} = 50 \text{ V}, V_{GE} = 0, f = 1 \text{MHz}$	_	850		pF
Switching time	Rise time	tr	Inductive Load		0.05		μS
	Turn-on time	t _{on}	$V_{CC} = 600 \text{ V}, \text{ I}_{C} = 15 \text{ A}$		0.12		
	Fall time	t _f	V_{GG} = ±15 V, R_G = 56 Ω		0.16	0.32	
	Turn-off time	t _{off}	(Note1)	_	0.56		
Thermal resistance		R _{th (j-c)}	—	_		0.74	°C/W

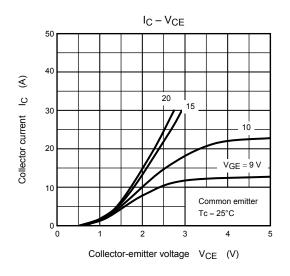
Note1: Switching time measurement circuit and input/output waveforms

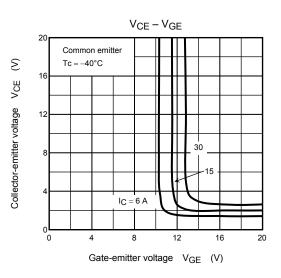


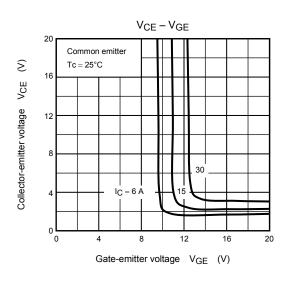
Note2: Switching loss measurement waveforms

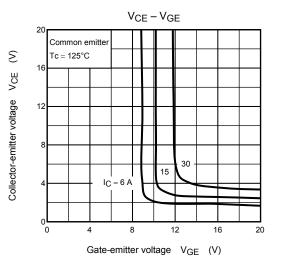


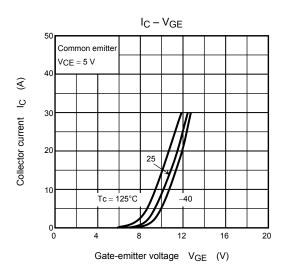
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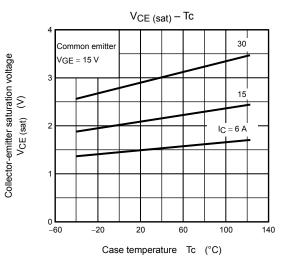




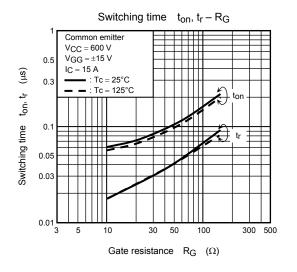


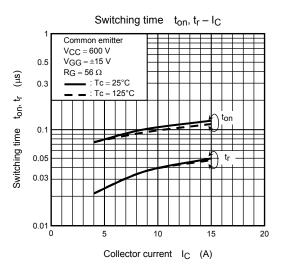




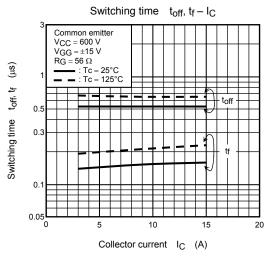


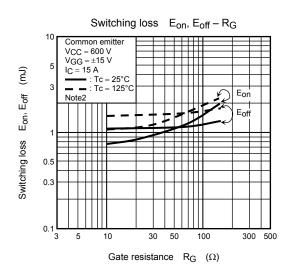
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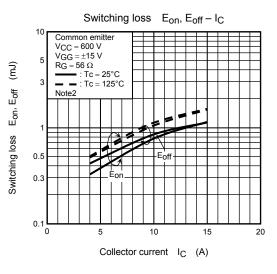




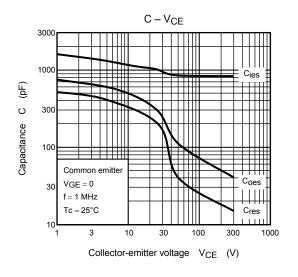
Switching time $t_{off}, t_f - R_G$ Common emitter $V_{CC} = 600 V$ $V_{GG} = \pm 15 V$ $I_C = 15 A$ $\therefore T_C = 25^{\circ}C$ $- \therefore T_C = 125^{\circ}C$ (ms) toff t_{off}, tf 0.5 Switching time 0.3 -tf 0.1 0.05 300 5 30 50 3 10 100 Gate resistance R_G (Ω)

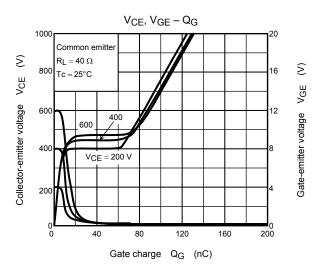






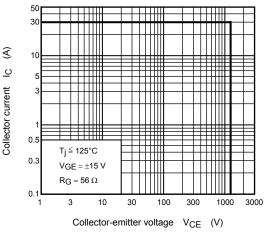
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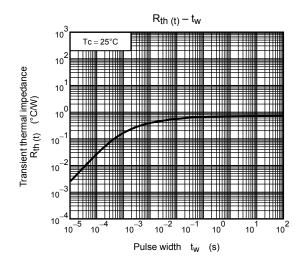




Safe operating area 100 50 IC max (pulsed)* 30 50 μs IC max (continuous) € 100 μ 10 <u>ں</u> DC operation Collector current *:Single nonrepetitive pr Tc = 25°C 0.5 Curves must be derated linearly with 0.3 increase in temperature 0.1 3 10 30 100 300 1000 3000 Collector-emitter voltage V_{CE} (V)

Reverse bias SOA





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20070701-EN

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